

SKW Associates, Inc.

3370 Victor Court

Santa Clara, CA 95054

Phone: (408) 919-0094

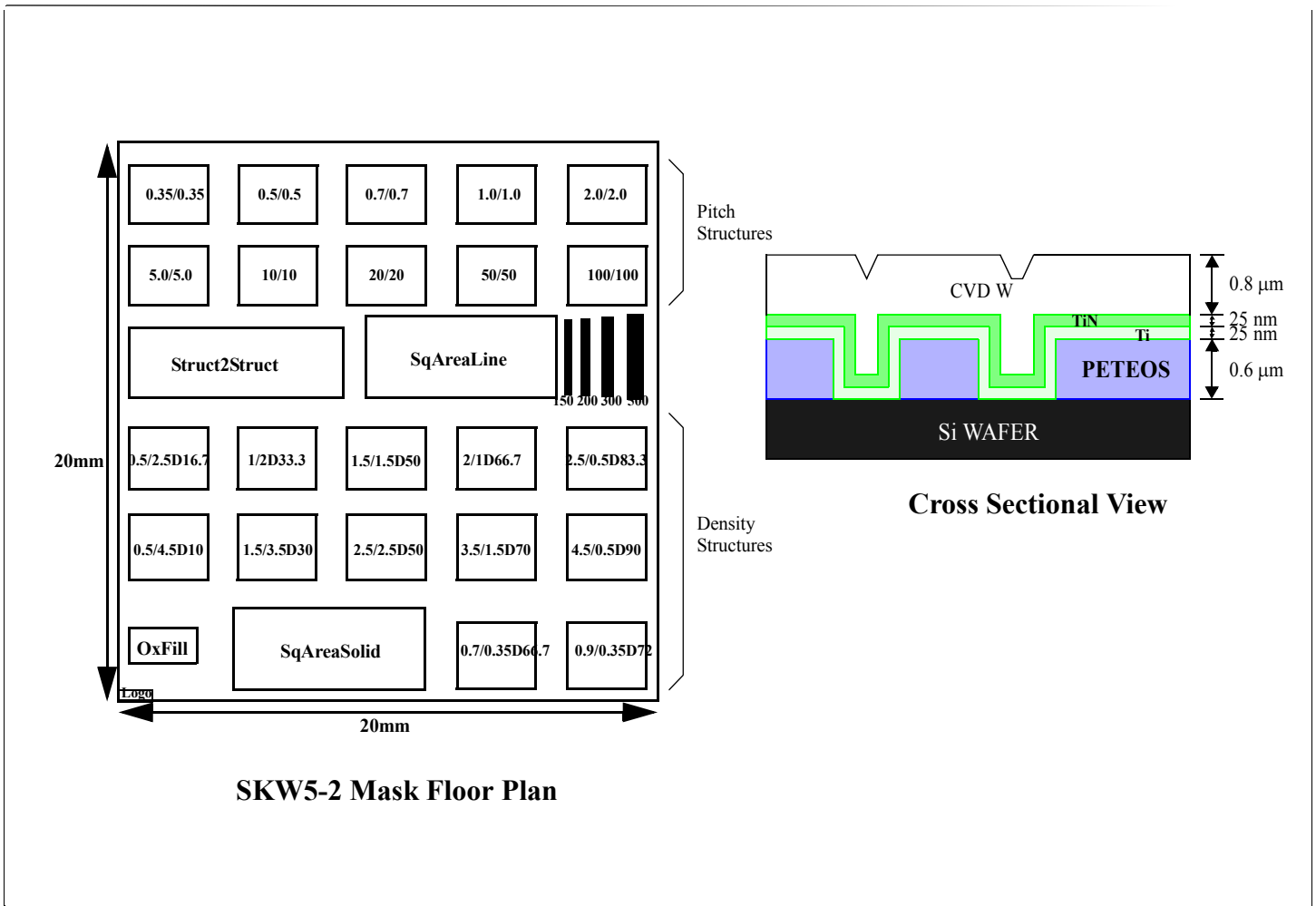
Fax: (408) 919-0097

Email: skw@testwafer.com

<http://www.testwafer.com>

SKW 5-2 Wafer Specifications

DATE: April 21, 2000



SKW5-2 Mask Floor Plan

Oxide Deposition

PARAMETER	NOMINAL	TOLERANCE
<i>PETEOS Thickness</i>		
Lot-to-Lot	6,000 Å	+/- 5 %
Within-Lot (Wafer-to-Wafer)		+/- 5 %
Within-Wafer		+/- 3 %
Within-Die		+/- 3 %

Ti Deposition

PARAMETER	NOMINAL	TOLERANCE
<i>Ti PVD Film Thickness</i>		
Lot-to-Lot	250 Å	+/- 5 %
Within-Lot (Wafer-to-Wafer)		+/- 5 %
Within-Wafer		+/- 5 %
Within-Die		+/- 5 %

TiN Deposition

PARAMETER	NOMINAL	TOLERANCE
<i>TiN PVD Film Thickness</i>		
Lot-to-Lot	250 Å	+/- 5 %
Within-Lot (Wafer-to-Wafer)		+/- 5 %
Within-Wafer		+/- 5 %
Within-Die		+/- 5 %

CVD W Film Deposition

PARAMETER	NOMINAL	TOLERANCE
<i>CVD W Film Thickness</i>		
Lot-to-Lot	8000 Å	+/- 10 %
Within-Lot (Wafer-to-Wafer)		+/- 10 %
Within-Wafer		+/- 5 %

Within-Die		+/- 5 %
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Patterning

PARAMETER	NOMINAL	TOLERANCE
<i>Patterning</i>		
Center Die X Location	-10.000 mm	+/- 100 μm
Center Die Y Location	-10.000 mm	+/- 100 μm
Die Size: X	20 mm	+/- 10 μm
Die Size: Y	20 mm	+/- 10 μm
Vertical Die Spacing	180 μm	+/- 10 %
Horizaontal Spacing	360 μm	+/- 10 %
<i>LineWidth Variation (measured on 2 μm structures)</i>		
Lot-to-Lot	2 μm	+/- 0.1 μm
Within-Lot (Wafer-to-Wafer)		+/- 0.1 μm
Within-Wafer		+/- 0.1 μm
Within-Die		+/- 0.1 μm